

# $I^2C^{\otimes}$ CMOS 8 × 8 Unbuffered Analog Switch Array with Dual/Single Supplies

**ADG2188** 

#### **FEATURES**

I<sup>2</sup>C-compatible interface
3.4 MHz high speed I<sup>2</sup>C option
32-lead LFCSP\_VQ (5 mm × 5 mm)
Double-buffered input logic
Simultaneous update of multiple switches
Up to 300 MHz bandwidth
Fully specified at dual ±5 V/single +12 V operation
On resistance 35 Ω maximum
Low quiescent current < 20 μA

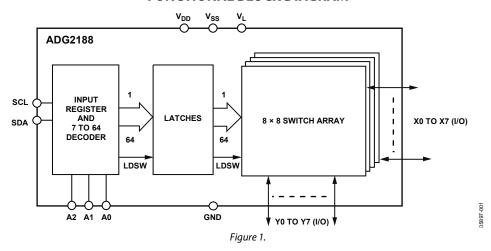
#### **APPLICATIONS**

AV switching in TV
Automotive infotainment
AV receivers
CCTV
Ultrasound applications
KVM switching
Telecom applications
Test equipment/instrumentation
PBX systems

#### **GENERAL DESCRIPTION**

The ADG2188 is an analog cross point switch with an array size of  $8\times 8$ . The switch array is arranged so that there are eight columns by eight rows, for a total of 64 switch channels. The array is bidirectional, and the rows and columns can be configured as either inputs or outputs. Each of the 64 switches can be addressed and configured through the I²C-compatible interface. Standard, full speed, and high speed (3.4 MHz) I²C interfaces are supported. Any simultaneous switch combination is allowed. An additional feature of the ADG2188 is that switches can be updated simultaneously, using the LDSW command. In addition, a  $\overline{\text{RESET}}$  option allows all of the switch channels to be reset/off. At power on, all switches are in the off condition. The device is packaged in a 32-lead,  $5 \text{ mm} \times 5 \text{ mm}$  LFCSP\_VQ.

#### **FUNCTIONAL BLOCK DIAGRAM**



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### **REVISION HISTORY**

4/06—Revision 0: Initial Version

## **SPECIFICATIONS**

 $V_{DD} = 12~V~\pm~10\%,~V_{SS} = 0~V,~V_L = 5~V,~GND = 0~V,~all~specifications~T_{MIN}~to~T_{MAX},~unless~otherwise~noted.~^1~MIN~to~T_{MAX},~unless~otherwise~noted.~^2~T_{MIN}~to~T_{MIN}~to~T_{MIN$ 

Table 1.

3.5 4 3.5 5 Ω max		BV	ersion	Y Version			
ANALOG SWITCH			−40°C to		−40°C to		
Analog Signal Range On Resistance, Ron On Resistance, Ron On Resistance, Ron On Resistance, Ron On Resistance Matching Between Channels, ΔRon On Resistance Flatness, Rounino On O	Parameter	+25°C	+85°C	+25°C	+125°C	Unit	Conditions
On Resistance, R <sub>ON</sub> 30  35  40  35  40  35  40  35  40  35  40  35  40  35  40  36  37  42  37  42  37  47  45  45  45  45  45  45  45  45  4	ANALOG SWITCH						
35	Analog Signal Range		$V_{\text{DD}}-2V$		$V_{\text{DD}}-2V$	V max	
32   37	On Resistance, Ron	30		30		Ω typ	$V_{DD} = 10.8 \text{ V}, V_{IN} = 0 \text{ V}, I_{S} = -10 \text{ mA}$
37		35	40	35	42	Ω max	
0 n Resistance Matching Between Channels, ΔRo <sub>N</sub> On Resistance Flatness, R <sub>FLATION</sub> Between Channels, ΔRo <sub>N</sub> On Resistance Flatness, R <sub>FLATION</sub> Between Channels, ΔRo <sub>N</sub> On Resistance Flatness, R <sub>FLATION</sub> On Resistance Flatness, R <sub>FLATION</sub> Between Channels, ΔRo <sub>N</sub> On Resistance Flatness, R <sub>FLATION</sub> As 9 8 10 Ωmax On Resistance Flatness, R <sub>FLATION</sub> On Resistance Flatness, R <sub>FLATION</sub> As 9 8 10 Ωmax On typ VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, I <sub>S</sub> = −10 m. As 2.3 Ωtyp VoD = 10.8 V, I <sub>S</sub> = −10 m. As 2.4 Ωtyp VoD = 10.8 V,		32		32		Ω typ	$V_{DD} = 10.8 \text{ V}, V_{IN} = 1.4 \text{ V}, I_{S} = -10 \text{ mA}$
On Resistance Matching Between Channels, ΔR <sub>ON</sub> 4.5         4.5         Ω τyp         V <sub>00</sub> = 10.8 V, V <sub>N</sub> = 0 V, I <sub>S</sub> = −10 mA           On Resistance Flatness, R <sub>FLATION</sub> On Ray On Road On Resistance Flatness, R <sub>FLATION</sub> On Ray On Road On Ray On Road On Ray On Road On Ray On Ray On Road On Ray On Road On Ray On Road On Ray		37	42	37	47	Ω max	
On Resistance Matching Between Channels, ΔRoN On Resistance Flatness, R <sub>ILATICNN</sub> 4.5         α typ Ω max         V <sub>DD</sub> = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 mA           On Resistance Flatness, R <sub>ILATICNN</sub> 2.3         2.3         Ω typ         V <sub>DD</sub> = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m           3.5         4         3.5         5         Ω max         Ω typ         V <sub>DD</sub> = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m           LEAKAGE CURRENTS Channel Off Leakage, Ion Channel Off Leakage, Ion Channel On Leakage, Ion Channel On Leakage, Ion Channel On Leakage, Ion Tho         ±0.03         ±0.03         ±0.03         µA typ         V <sub>DD</sub> = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m           DYNAMIC CHARACTERISTICS <sup>2</sup> Corr         ±0.03         ±0.03         ±0.03         µA typ         V <sub>VD</sub> = 10.8 V, V <sub>N</sub> = 0 V to 5.4 V, I <sub>S</sub> = −10 m           Corr         11         11         11         pA typ         V <sub>VD</sub> = 10.8 V, V <sub>N</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m           DYNAMIC CHARACTERISTICS <sup>2</sup> ±0.03         ±0.03         µA typ         V <sub>VD</sub> = 10.8 V, V <sub>N</sub> = 0 V to 5.4 V, I <sub>S</sub> = −10 m           Corr         11         11         11         pF typ         PF typ         N <sub>E</sub> = 300 Ω, C <sub>L</sub> = 35 pF         N <sub>E</sub> = 300 Ω, C <sub>L</sub> = 35 pF         N <sub>E</sub> = 300 Ω, C <sub>L</sub> = 35 pF         N <sub>E</sub> = 300 Ω, C <sub>L</sub> = 35 pF         N <sub>E</sub> = 300 Ω, C <sub>L</sub> = 35 pF         N <sub>E</sub> = 300 Ω, C <sub>L</sub> = 35 pF         N <sub>E</sub> = 300 Ω, C <sub></sub>		45		45		Ω typ	$V_{DD} = 10.8 \text{ V}, V_{IN} = 5.4 \text{ V}, I_S = -10 \text{ mA}$
Between Channels, ΔRoN On Resistance Flatness, R <sub>IZATION</sub> I On Resistance Flatness, R <sub>IZATION</sub> I On Resistance Flatness, R <sub>IZATION</sub> I 14.5         8         9         8         10         Ω max Ω typ         V <sub>DD</sub> = 10.8 V, V <sub>IN</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m.           LEAKAGE CURRENTS Channel Off Leakage, Iosr Channel Off Leakage, Iosr Channel On Leakage, Iosn DYNAMIC CHARACTERISTICS²         ±0.03 ±0.03         ±0.03 ±0.03         µA typ µA typ         V <sub>DD</sub> = 13.2 V V≈ 7 V/1 V, V≈ 1 V/7 V           Corr Corr Con         11 18.5         ±0.03 ±0.03         µA typ         Vx = 7 V/1 V, V ≈ 1 V/7 V           DYNAMIC CHARACTERISTICS²         11 10 10 10 10 10 10 10 10 10 10 10 10 1		50	57	50	62	Ω max	
On Resistance Flatness, R <sub>FLATION</sub> 1         2.3         2.3         Ω typ (Ω max) (Ω typ (Ω max) (Ω typ (Ω max))         V <sub>DD</sub> = 10.8 V, V <sub>IN</sub> = 0 V to 1.4 V, I <sub>S</sub> = −10 m. (Ω typ (Ω max))           LEAKAGE CURRENTS Channel Off Leakage, IorF Channel Off Leakage, IorD Channel On Leakage, IorD Channel Channels On Channels O	On Resistance Matching	4.5		4.5		Ωtyp	$V_{DD} = 10.8 \text{ V}, V_{IN} = 0 \text{ V}, I_S = -10 \text{ mA}$
3.5	Between Channels, ΔR <sub>ON</sub>	8	9	8	10	Ω max	
3.5	On Resistance Flatness, R <sub>FLAT(ON)</sub>	2.3		2.3		Ωtyp	$V_{DD} = 10.8 \text{ V}, V_{IN} = 0 \text{ V to } 1.4 \text{ V}, I_S = -10 \text{ mA}$
14.5		3.5	4	3.5	5	Ω max	
LEAKAGE CURRENTS         ±0.03         ±0.03         ±0.03         μA typ         V <sub>DD</sub> = 13.2 V           Channel Off Leakage, losr         ±0.03         ±0.03         μA typ         V <sub>x</sub> = 7 V/1 V, V <sub>Y</sub> = 1 V/7 V           DYNAMIC CHARACTERISTICS²         2         2         2         2         2         2         2         2         2         2         2         1 V <sub>x</sub> = 1 V <sub>y</sub> V <sub>x</sub> = 1 V <sub>y</sub> V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 2         1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 2         1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 2         1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 2         1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 2         1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 2         1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 2         1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 2         1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 2         1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 2         1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 2         1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 1 V <sub>y</sub> = 1 V <sub>y</sub> V <sub>y</sub> 1 V <sub>y</sub> P <sub>y</sub> 2 V <sub>y</sub>		14.5		14.5		Ωtyp	$V_{DD} = 10.8 \text{ V}, V_{IN} = 0 \text{ V to } 5.4 \text{ V}, I_S = -10 \text{ mA}$
LEAKAGE CURRENTS         Channel Off Leakage, IorF         ±0.03         ±0.03         μA typ         V <sub>D</sub> = 13.2 V         V <sub>X</sub> = 7 V/1 V, V <sub>Y</sub> = 1 V/7 V         V <sub>X</sub> = 7 V/1 V, V <sub>Y</sub> = 1 V/7 V         V <sub>X</sub> = 7 V/1 V, V <sub>Y</sub> = 1 V/7 V         V <sub>X</sub> = 7 V/1 V, V <sub>Y</sub> = 1 V/7 V         V <sub>X</sub> = 7 V/1 V, V <sub>Y</sub> = 1 V/7 V         V <sub>X</sub> = 7 V/1 V, V <sub>Y</sub> = 1 V/7 V         V <sub>X</sub> = 7 V/1 V, V <sub>Y</sub> = 1 V/7 V         V <sub>X</sub> = 7 V/1 V, V <sub>Y</sub> = 1 V/7 V         V <sub>X</sub> = 7 V/1 V, V <sub>Y</sub> = 1 V/7 V         V <sub>X</sub> = 7 V/1 V, V <sub>Y</sub> = 1 V/7 V         V <sub>X</sub> = 7 V/1 V, V <sub>Y</sub> = 1 V/7 V         V <sub>X</sub> = 7 V/1 V, V <sub>Y</sub> = 1 V/7 V         V <sub>X</sub> = 1 V/7 V		18	20	18	22		
Channel Off Leakage, Iorr Channel On Leakage, Ion         ±0.03         ±0.03         μA typ         Vx = 7V/1V, Vy = 1 V/7V           DYNAMIC CHARACTERISTICS²         20.03         ±0.03         μA typ         Vx = Vy = 1 V or 7 V           Core Lon         11         11         pF typ         Vx = Vy = 1 V or 7 V           Core Lon         18.5         18.5         pF typ         PF typ           Lon         170         170         ns typ         RL = 300 Ω, CL = 35 pF           Lon         185         190         185         195         ns max           Lon         210         210         ns max         RL = 300 Ω, CL = 35 pF           THD + N         0.04         250         255         250         260         ns max           THD + N         0.04         0.04         % typ         RL = 10 kΩ, f = 20 Hz to 20 kHz, Vs = 1 Vp - P           PSRR         90         dB typ         F = 20 kHz; without decoupling; see Figure 24           -3 dB Bandwidth         210         MHz typ         Individual inputs to outputs           Off Isolation         -69         -69         dB typ         RL = 75 Ω, CL = 5 pF, f = 5 MHz           Adjacent Channels         -63         dB typ         RL = 75 Ω, CL = 5 pF, f = 5 MHz	LEAKAGE CURRENTS						V <sub>DD</sub> = 13.2 V
Channel On Leakage, IoN         ±0.03         ±0.03         μA typ         Vx = Vy = 1 V or 7 V           DYNAMIC CHARACTERISTICS²         CoFF         11         11         pF typ         TO           CoFF         11         18.5         pF typ         ns typ         RL = 300 Ω, CL = 35 pF           toN         170         170         ns typ         RL = 300 Ω, CL = 35 pF           185         190         185         195         ns max           toFF         210         210         ns typ         RL = 300 Ω, CL = 35 pF           THD + N         0.04         0.04         % typ         RL = 10 kΩ, f = 20 Hz to 20 kHz, Vs = 1 V p-p           PSRR         90         dB typ         F = 20 kHz; without decoupling; see Figure 24           -3 dB Bandwidth         210         210         MHz typ         Individual inputs to outputs           Off Isolation         -69         -69         dB typ         Rinputs to 1 output           Off Isolation         -69         -69         dB typ         RL = 75 Ω, CL = 5 pF, f = 5 MHz           Channel-to-Channel Crosstalk         Adjacent Channels         -63         dB typ           Nonadjacent Channels         -76         dB typ           Differential Gain         0.4		±0.03		±0.03		uA tvp	
DYNAMIC CHARACTERISTICS <sup>2</sup> C <sub>OFF</sub> 11         11         pF typ           C <sub>ON</sub> 18.5         18.5         pF typ           t <sub>ON</sub> 170         170         ns typ         R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF           t <sub>OFF</sub> 210         210         ns max           t <sub>OFF</sub> 250         255         250         260         ns max           THD + N         0.04         0.04         % typ         R <sub>L</sub> = 10 kΩ, f = 20 Hz to 20 kHz, Vs = 1 V p-p           PSRR         90         dB typ         f = 20 kHz; without decoupling; see Figure 24           -3 dB Bandwidth         210         210         MHz typ         Individual inputs to outputs           Off Isolation         -69         -69         dB typ         R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz           Channel-to-Channel Crosstalk         Adjacent Channels         -63         -63         dB typ           Nonadjacent Channels         -76         -76         dB typ           Differential Gain         0.4         0.4         % typ         R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz           Charge Injection         -3.5         -3.5         pC typ         Vs = 4 V, R <sub>S</sub> = 0 Ω, C <sub>L</sub> = 1 nF           LOGIC INPUTS (Ax, RESET)² </td <td>_</td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td>	_						
CoFF         11         11         pF typ         PF typ           CoN         18.5         18.5         pF typ         PF typ           toN         170         170         ns typ         RL = 300 Ω, CL = 35 pF           185         190         185         195         ns max           toFF         210         210         ns max           THD + N         0.04         0.04         % typ         RL = 300 Ω, CL = 35 pF           PSRR         90         dB typ         Fk typ p         RL = 10 kΩ, f = 20 Hz to 20 kHz, Vs = 1 Vp - p           PSRR         90         dB typ         f = 20 kHz; without decoupling; see Figure 24           -3 dB Bandwidth         210         210         MHz typ         Individual inputs to outputs           Off Isolation         -69         -69         dB typ         RL = 75 Ω, CL = 5 pF, f = 5 MHz           Channel-to-Channel Crosstalk         Adjacent Channels         -63         -63         dB typ           Nonadjacent Channels         -76         -76         dB typ           Differential Gain         0.4         0.4         % typ         RL = 75 Ω, CL = 5 pF, f = 5 MHz           Differential Phase         0.6         0.6         °typ         RL = 75 Ω, CL = 5 p						P / P	
Con       18.5       18.5       18.5       pF typ ns max       R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF         toff       210       210       ns typ ns max       R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF         THD + N       250       255       250       260       ns max         THD + N       0.04       0.04       % typ ys ns max       R <sub>L</sub> = 10 kΩ, f = 20 Hz to 20 kHz, V <sub>S</sub> = 1 V p-p         PSRR       90       dB typ ys ns max       f = 20 kHz; without decoupling; see Figure 24         -3 dB Bandwidth       210       210       MHz typ Individual inputs to outputs         Off Isolation       -69       -69       dB typ R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz         Channel-to-Channel Crosstalk       -69       -69       dB typ R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz         Adjacent Channels       -76       -76       dB typ R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz         Differential Gain       0.4       0.4       % typ R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz         Differential Phase       0.6       0.6       ° typ R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz         Charge Injection       -3.5       -3.5       pC typ Vs = 4V, Rs = 0 Ω, C <sub>L</sub> = 1 nF         LOGIC INPUTS (Ax, RESET)²       0.8       0.8       V max         Input Hig		11		11		pF typ	
ton       170       170       ns typ       R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF         toff       185       190       185       195       ns max         toff       210       210       ns typ       R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF         THD + N       0.04       0.04       % typ       R <sub>L</sub> = 10 kΩ, f = 20 Hz to 20 kHz, V <sub>S</sub> = 1 V p-p         PSRR       90       dB typ       f = 20 kHz; without decoupling; see Figure 24         -3 dB Bandwidth       210       210       MHz typ       Individual inputs to outputs         Off Isolation       -69       -69       dB typ       8 inputs to 1 output         Off Isolation       -69       -69       dB typ       R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz         Channel-to-Channel Crosstalk       -63       -63       dB typ         Adjacent Channels       -63       -63       dB typ         Nonadjacent Channels       -76       dB typ         Differential Gain       0.4       0.4       % typ         Differential Phase       0.6       0.6       ° typ       R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz         Charge Injection       -3.5       -3.5       pC typ       V <sub>S</sub> = 4V, R <sub>S</sub> = 0 Ω, C <sub>L</sub> = 1 nF         LOGIC INPUTS (Ax, RESET)²       Input High Voltage, V							
toff       185       190       185       195       ns max ns typ ns max ns typ ns max       R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF         THD + N       0.04       0.04       % typ with typ ns max       R <sub>L</sub> = 10 kΩ, f = 20 Hz to 20 kHz, V <sub>S</sub> = 1 V p-p         PSRR       90       dB typ f = 20 kHz; without decoupling; see Figure 24         -3 dB Bandwidth       210       210       MHz typ lndividual inputs to outputs         Off Isolation       -69       -69       dB typ lndividual inputs to outputs         Channel-to-Channel Crosstalk Adjacent Channels       -69       dB typ lndividual inputs to outputs         Nonadjacent Channels       -63       -63       dB typ lndividual inputs to outputs         Nonadjacent Channel Crosstalk Adjacent Channels       -69       dB typ lndividual inputs to outputs         Nonadjacent Channels       -69       dB typ lndividual inputs to outputs         Nonadjacent Channels       -69       dB typ lndividual inputs to outputs         Nonadjacent Channels       -63       -63       dB typ lndividual inputs to outputs         Nonadjacent Channels       -63       -63       dB typ lndividual inputs to outputs         Nonadjacent Channels       -63       -63       dB typ lndividual inputs to outputs         Nonadjacent Channels       -63       -63       dB typ lndividual							R <sub>1</sub> = 300 O C <sub>1</sub> = 35 pF
toff       210       210       ns typ       R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF         THD + N       0.04       0.04       0.04       % typ       R <sub>L</sub> = 10 kΩ, f = 20 Hz to 20 kHz, Vs = 1 V p-p         PSRR       90       dB typ       f = 20 kHz; without decoupling; see Figure 24         -3 dB Bandwidth       210       MHz typ       Individual inputs to outputs         0ff Isolation       16.5       16.5       MHz typ       8 inputs to 1 output         0ff Isolation       -69       -69       dB typ       R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz         Channel-to-Channel Crosstalk       Adjacent Channels       -63       -63       dB typ         Nonadjacent Channels       -76       -76       dB typ         Differential Gain       0.4       0.4       % typ       R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz         Differential Phase       0.6       0.6       ° typ       R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz         Charge Injection       -3.5       -3.5       pC typ       Vs = 4 V, Rs = 0 Ω, C <sub>L</sub> = 1 nF         LOGIC INPUTS (Ax, RESET)²       0.8       0.8       V max         Input Leakage Current, I <sub>IN</sub> 0.005       0.005       V min	CON		190	-	195		112 300 127 CE 33 PI
THD + N       250       255       250       260       ns max       R <sub>L</sub> = 10 kΩ, f = 20 Hz to 20 kHz, V <sub>s</sub> = 1 V p-p         PSRR       90       dB typ       f = 20 kHz; without decoupling; see Figure 24         -3 dB Bandwidth       210       210       MHz typ       Individual inputs to outputs to outputs         Off Isolation       16.5       16.5       MHz typ       8 inputs to 1 output         Off Isolation       -69       -69       dB typ       R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz         Channel-to-Channel Crosstalk       Adjacent Channels       -63       dB typ       R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz         Adjacent Channels       -76       -76       dB typ       R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz         Differential Gain       0.4       0.4       % typ       R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz         Differential Phase       0.6       0.6       ° typ       R <sub>L</sub> = 75 Ω, C <sub>L</sub> = 5 pF, f = 5 MHz         Charge Injection       -3.5       -3.5       pC typ       V <sub>S</sub> = 4 V, R <sub>S</sub> = 0 Ω, C <sub>L</sub> = 1 nF         LOGIC INPUTS (Ax, RESET)²       Input High Voltage, V <sub>INL</sub> 0.8       V min         Input Leakage Current, In       0.005       0.005       V min	†off		150		.55		R <sub>I</sub> = 300 O C <sub>I</sub> = 35 pF
THD + N       0.04       0.04       % typ $R_L = 10 \text{ kΩ}$ , $f = 20 \text{ Hz}$ to 20 kHz, $V_S = 1 \text{ V p-p}$ PSRR       90       dB typ $f = 20 \text{ kHz}$ ; without decoupling; see Figure 24         -3 dB Bandwidth       210       MHz typ       Individual inputs to outputs         0ff Isolation       -69       -69       dB typ       8 inputs to 1 output         0ff Isolation       -69       -69       dB typ $R_L = 75 \Omega$ , $C_L = 5 \text{ pF}$ , $f = 5 \text{ MHz}$ Channel-to-Channel Crosstalk       -63       dB typ $R_L = 75 \Omega$ , $C_L = 5 \text{ pF}$ , $f = 5 \text{ MHz}$ Adjacent Channels       -76       -76       dB typ         Differential Gain       0.4       0.4       % typ $R_L = 75 \Omega$ , $C_L = 5 \text{ pF}$ , $f = 5 \text{ MHz}$ Differential Phase       0.6       0.6       ° typ $R_L = 75 \Omega$ , $C_L = 5 \text{ pF}$ , $f = 5 \text{ MHz}$ Charge Injection       -3.5       -3.5       pC typ $V_S = 4 V$ , $V_S = 0 \Omega$ , $V_S = 4 V$ , $V_S = 0 \Omega$ LOGIC INPUTS (Ax, RESET)²       0.8       0.8       0.8       0.8       0.8         Input Leakage Current, $V_S = 0 \Omega$ 0.005       0.005       0.005       0.005       0.005	COLL		255		260	1 ''	112 300 127 CE 33 PI
PSRR       90       dB typ $f = 20 \text{ kHz}$ ; without decoupling; see Figure 24         -3 dB Bandwidth       210       MHz typ       Individual inputs to outputs         0ff Isolation       -69       -69       dB typ       8 inputs to 1 output         Channel-to-Channel Crosstalk       -69       -69       dB typ $R_L = 75 \Omega$ , $C_L = 5 pF$ , $f = 5 MHz$ Adjacent Channels       -63       -63       dB typ         Nonadjacent Channels       -76       -76       dB typ         Differential Gain       0.4       0.4       % typ $R_L = 75 \Omega$ , $C_L = 5 pF$ , $f = 5 MHz$ Differential Phase       0.6       0.6       ° typ $R_L = 75 \Omega$ , $C_L = 5 pF$ , $f = 5 MHz$ Charge Injection       -3.5       -3.5       pC typ $V_S = 4V$ , $V_S = 0 \Omega$ , $V_S = 4V$ , $V_S = 0 \Omega$ , $V_S = 4V$ , $V_S = 0 \Omega$ , $V_S = 4V$ , $V_S = 0 \Omega$ , $V_S $	THD + N				200		
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	PSRR			90		dB typ	f = 20 kHz; without decoupling;
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	−3 dB Bandwidth	210		210		MHz typ	
Off Isolation $-69$ $-69$ dB typ $R_L = 75 \Omega$ , $C_L = 5 pF$ , $f = 5 MHz$ Channel-to-Channel Crosstalk $-63$ $-63$ dB typ         Adjacent Channels $-63$ $-63$ dB typ         Nonadjacent Channels $-76$ $-76$ dB typ         Differential Gain $0.4$ $0.4$ $96$ typ $R_L = 75 \Omega$ , $C_L = 5 pF$ , $f = 5 MHz$ Differential Phase $0.6$		16.5		16.5		MHz typ	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Off Isolation	-69		-69			$R_L = 75 \Omega$ , $C_L = 5 pF$ , $f = 5 MHz$
Adjacent Channels $-63$ $-63$ dB typ         Nonadjacent Channels $-76$ $-76$ dB typ         Differential Gain $0.4$ $0.4$ % typ $R_L = 75 \Omega$ , $C_L = 5 pF$ , $f = 5 MHz$ Differential Phase $0.6$ $0.6$ ° typ $R_L = 75 \Omega$ , $C_L = 5 pF$ , $f = 5 MHz$ Charge Injection $-3.5$ $-3.5$ pC typ $V_S = 4 V$ , $R_S = 0 \Omega$ , $C_L = 1 nF$ LOGIC INPUTS (Ax, RESET)²       Input High Voltage, $V_{INH}$ $0.8$ $0.8$ $V_I$ min         Input Low Voltage, $V_{INL}$ $0.8$ $0.8$ $V_I$ max         Input Leakage Current, $I_{IN}$ $0.005$ $0.005$ $0.005$	Channel-to-Channel Crosstalk					,	
Nonadjacent Channels $-76$	Adjacent Channels	-63		-63		dB typ	
Differential Gain       0.4       0.4       % typ $R_L = 75 \Omega$ , $C_L = 5 pF$ , $f = 5 MHz$ Differential Phase       0.6       0.6       ° typ $R_L = 75 \Omega$ , $C_L = 5 pF$ , $f = 5 MHz$ Charge Injection       -3.5       -3.5       pC typ $V_S = 4 V$ , $R_S = 0 \Omega$ , $C_L = 1 nF$ LOGIC INPUTS (Ax, RESET)²       Input High Voltage, $V_{INH}$ 2.0       2.0 $V_{INH}$ Input Low Voltage, $V_{INL}$ 0.8       0.8 $V_{INL}$ Input Leakage Current, $I_{IN}$ 0.005       0.005 $\mu A$ typ		-76		-76			
Differential Phase 0.6 0.6 ° typ $R_L = 75 \Omega$ , $C_L = 5$ pF, $f = 5$ MHz Charge Injection $-3.5$ $-3.5$ ° pC typ $V_S = 4$ V, $R_S = 0 \Omega$ , $C_L = 1$ nF LOGIC INPUTS (Ax, RESET) <sup>2</sup> Input High Voltage, $V_{INH}$ 2.0 2.0 V min Input Low Voltage, $V_{INL}$ 0.8 0.8 V max Input Leakage Current, $I_{IN}$ 0.005 0.005 $\mu$ A typ							$R_L = 75 \Omega$ , $C_L = 5 pF$ , $f = 5 MHz$
Charge Injection $-3.5$ $-3.5$ pC typ $V_S = 4 \text{ V}$ , $R_S = 0 \Omega$ , $C_L = 1 \text{ nF}$ LOGIC INPUTS (Ax, RESET)²Input High Voltage, $V_{\text{INH}}$ $2.0$ $2.0$ $V \text{ min}$ Input Low Voltage, $V_{\text{INL}}$ $0.8$ $0.8$ $V \text{ max}$ Input Leakage Current, $I_{\text{IN}}$ $0.005$ $0.005$ $\mu A \text{ typ}$							
LOGIC INPUTS (Ax, RESET)²       2.0       2.0       V min         Input High Voltage, V <sub>INL</sub> 0.8       0.8       V max         Input Leakage Current, I <sub>IN</sub> 0.005       0.005       μA typ							
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$						''	
Input Low Voltage, V <sub>INL</sub> 0.8         0.8         V max           Input Leakage Current, I <sub>IN</sub> 0.005         0.005         μA typ			2.0		2.0	V min	
Input Leakage Current, I <sub>IN</sub> 0.005 0.005 μA typ							
		0.005	•••	0.005	•••		
	pac zeanage carrein, iii	0.505	+1	0.003	+1		
Input Capacitance, C <sub>IN</sub> 7 7 pF typ	Input Capacitance Co	7		7		-	

	B Version		YY	/ersion		
		−40°C to		−40°C to		
Parameter	+25°C	+85°C	+25°C	+125°C	Unit	Conditions
LOGIC INPUTS (SCL, SDA) <sup>2</sup>						
Input High Voltage, V <sub>INH</sub>		$0.7~V_{\textrm{L}}$		0.7 V <sub>L</sub>	V min	
		$V_L + 0.3$		$V_{L} + 0.3$	V max	
Input Low Voltage, V <sub>INL</sub>		-0.3		-0.3	V min	
		$0.3V_L$		0.3 V <sub>L</sub>	V max	
Input Leakage Current, I <sub>IN</sub>	0.005		0.005		μA typ	$V_{IN} = 0 V to V_L$
		±1		±1	μA max	
Input Hysteresis		$0.05V_L$		0.05 V <sub>L</sub>	V min	
Input Capacitance, C <sub>IN</sub>	7		7		pF typ	
LOGIC OUTPUT (SDA) <sup>2</sup>						
Output Low Voltage, V <sub>OL</sub>		0.4		0.4	V max	I <sub>SINK</sub> = 3 mA
		0.6		0.6	V max	I <sub>SINK</sub> = 6 mA
Floating State Leakage Current		±1		±1	μA max	
POWER REQUIREMENTS						
I <sub>DD</sub>	0.05		0.05		μA typ	Digital inputs = 0 V or V <sub>L</sub>
		1		1	μA max	
Iss	0.05		0.05		μA typ	Digital inputs = 0 V or V <sub>L</sub>
		1		1	μA max	
l <sub>L</sub>						Digital inputs = 0 V or V <sub>L</sub>
Interface Inactive	0.3		0.3		μA typ	
		2		2	μA max	
Interface Active: 400 kHz fscl	0.1		0.1		mA typ	
		0.2		0.2	mA max	
Interface Active: 3.4 MHz fscl	0.4		0.4		mA typ	-HS model only
		1.2		1.7	mA max	

 $<sup>^1</sup>$  Temperature range is as follows: B version:  $-40^\circ\text{C}$  to  $+85^\circ\text{C};$  Y version:  $-40^\circ\text{C}$  to  $+125^\circ\text{C}.$   $^2$  Guaranteed by design, not subject to production test.

 $V_{DD}$  = +5 V  $\pm$  10% ,  $V_{SS}$  = -5 V  $\pm$  10% ,  $V_L$  = 5 V, GND = 0 V, all specifications  $T_{MIN}$  to  $T_{MAX}$ , unless otherwise noted. <sup>1</sup>

Table 2.

	B Version		YV	ersion		
		−40°C to		−40°C to		
Parameter	+25°C	+85°C	+25°C	+125°C	Unit	Conditions
ANALOG SWITCH						
Analog Signal Range				$V_{\text{DD}}-2V$	V max	
On Resistance, R <sub>ON</sub>	34		34		Ω typ	$V_{DD} = +4.5 \text{ V}, V_{SS} = -4.5 \text{ V}, V_{IN} = V_{SS}, I_S = -10 \text{ mA}$
	40	45	40	50	Ω max	
	50		50		Ω typ	$V_{DD} = +4.5 \text{ V}, V_{SS} = -4.5 \text{ V}, V_{IN} = 0 \text{ V}, I_S = -10 \text{ mA}$
	55	65	55	70	Ω max	
	66		66		Ω typ	$V_{DD} = +4.5 \text{ V}, V_{SS} = -4.5 \text{ V}, V_{IN} = +1.4 \text{ V}, I_S = -10 \text{ mA}$
	75	85	75	95	$\Omega$ max	
On Resistance Matching	4.5		4.5		Ωtyp	$V_{DD} = +4.5 \text{ V}, V_{SS} = -4.5 \text{ V}, V_{IN} = V_{SS}, I_S = -10 \text{ mA}$
Between Channels, ΔR <sub>ON</sub>	8	9	8	10	$\Omega$ max	
On Resistance Flatness, R <sub>FLAT(ON)</sub>	17		17		Ω typ	$V_{DD} = +4.5 \text{ V}, V_{SS} = -4.5 \text{ V}, V_{IN} = V_{SS} \text{ to } 0 \text{ V}, I_S = -10 \text{ mA}$
	20	23	20	25	$\Omega$ max	
	34		34		Ωtyp	$V_{DD} = +4.5 \text{ V}, V_{SS} = -4.5 \text{ V}, V_{IN} = V_{SS} \text{ to } +1.4 \text{ V}, \\ I_{S} = -10 \text{ mA}$
	42	45	42	48	Ω max	
LEAKAGE CURRENTS						$V_{DD} = 5.5 \text{ V}, V_{SS} = 5.5 \text{ V}$
Channel Off Leakage, IOFF	±0.03		±0.03		μA typ	$V_X = +4.5 \text{ V/}-2 \text{ V}, V_Y = -2 \text{ V/}+4.5 \text{ V}$
Channel On Leakage, Ion	±0.03		±0.03		μA typ	$V_X = V_Y = -2 \text{ V or } +4.5 \text{ V}$
DYNAMIC CHARACTERISTICS <sup>2</sup>						
C <sub>OFF</sub>	6		6		pF typ	
Con	9.5		9.5		pF typ	
ton	170		170		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$
	200	215	200	220	ns max	,
t <sub>OFF</sub>	210		210		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$
	250	255	250	260	ns max	·
THD + N	0.04		0.04		% typ	$R_L = 10 \text{ k}\Omega$ , $f = 20 \text{ Hz to } 20 \text{ kHz}$ , $V_S = 1 \text{ V p-p}$
PSRR			90		dB typ	f = 20 kHz; without decoupling; see Figure 24
–3 dB Bandwidth	300		300		MHz typ	Individual inputs to outputs
	18		18		MHz typ	8 inputs to 1 output
Off Isolation	-66		-64		dB typ	$R_L = 75 \Omega$ , $C_L = 5 pF$ , $f = 5 MHz$
Channel-to-Channel Crosstalk						$R_L = 75 \Omega$ , $C_L = 5 pF$ , $f = 5 MHz$
Adjacent Channels	-62		-62		dB typ	
Nonadjacent Channels	<b>-79</b>		-79		dB typ	
Differential Gain	1.5		1.5		% typ	$R_L = 75 \Omega$ , $C_L = 5 pF$ , $f = 5 MHz$
Differential Phase	1.8		1.8		°typ	$R_L = 75 \Omega$ , $C_L = 5 pF$ , $f = 5 MHz$
Charge Injection	-3		-3		pC typ	$V_S = 0 \text{ V}, R_S = 0 \Omega, C_L = 1 \text{ nF}$
LOGIC INPUTS (Ax, RESET) <sup>2</sup>					. ,.	
Input High Voltage, V <sub>INH</sub>		2.0		2.0	V min	
Input Low Voltage, V <sub>INL</sub>		0.8		0.8	V max	
Input Leakage Current, I <sub>IN</sub>	0.005	0.0	0.005	0.0	μA typ	
mpat Leanage Carrent, in	0.003	±1	0.003	±1	μA max	
Input Capacitance, C <sub>IN</sub>	7		7	<u>-</u> '	pF typ	
LOGIC INPUTS (SCL, SDA) <sup>2</sup>	=		-		F: -7 P	
Input High Voltage, V <sub>INH</sub>		0.7 V <sub>L</sub>		0.7 V <sub>L</sub>	V min	
		V <sub>L</sub> + 0.3		V <sub>L</sub> + 0.3	V max	
Input Low Voltage, V <sub>INL</sub>		-0.3		-0.3	V min	
		0.5	1			
mpar Low Voltage, VINL		0 3 V <sub>1</sub>		03V	I V max	
Input Leakage Current, I <sub>IN</sub>	0.005	0.3 V <sub>L</sub>	0.005	0.3 V <sub>L</sub>	V max μΑ typ	$V_{IN} = 0 V to V_L$

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	BV	ersion ersion	YV	ersion		
_		−40°C to		−40°C to		
Parameter	+25°C	+85°C	+25°C	+125°C	Unit	Conditions
Input Hysteresis		$0.05~V_{L}$		$0.05~V_{L}$	V min	
Input Capacitance, C <sub>IN</sub>	7		7		pF typ	
LOGIC OUTPUT (SDA) <sup>2</sup>						
Output Low Voltage, Vol		0.4		0.4	V max	I <sub>SINK</sub> = 3 mA
		0.6		0.6	V max	I <sub>SINK</sub> = 6 mA
Floating State Leakage Current		±1		±1	μA max	
POWER REQUIREMENTS						
$I_{DD}$	0.05		0.005		μA typ	Digital inputs = 0 V or V <sub>L</sub>
		1		1	μA max	
I <sub>SS</sub>	0.05		0.005		μA typ	Digital inputs = 0 V or V <sub>L</sub>
		1		1	μA max	
IL						Digital inputs = 0 V or V <sub>L</sub>
Interface Inactive	0.3		0.3		μA typ	
		2		2	μA max	
Interface Active: 400 kHz fscl	0.1		0.1		mA typ	
		0.1		0.1	mA max	
Interface Active: 3.4 MHz fscl	0.4		0.4		mA typ	-HS model only
		0.3		0.3	mA max	

 $<sup>^1</sup>$  Temperature range is as follows: B version: –40°C to +85°C; Y version: –40°C to +125°C.  $^2$  Guaranteed by design, not subject to production test.

### **I<sup>2</sup>C TIMING SPECIFICATIONS**

 $V_{DD} = 5 \text{ V}$  to 12 V;  $V_{SS} = -5 \text{ V}$  to 0 V;  $V_L = 5 \text{ V}$ ; GND = 0 V;  $T_A = T_{MIN}$  to  $T_{MAX}$ , unless otherwise noted (see Figure 2).

Table 3.

		ADG2188 I	Limit at T <sub>M</sub>	N, T <sub>MAX</sub>			
Parameter <sup>1</sup>	Conditions	Min	Max	Unit	Description		
f <sub>SCL</sub>	Standard mode		100	kHz	Serial clock frequency		
	Fast mode		400	kHz			
	High speed mode <sup>2</sup>						
	C <sub>B</sub> = 100 pF maximum		3.4	MHz			
	$C_B = 400 \text{ pF maximum}$		1.7	MHz			
t <sub>1</sub>	Standard mode	4		μs	t <sub>нібн</sub> , SCL high time		
	Fast mode	0.6		μs			
	High speed mode <sup>2</sup>						
	$C_B = 100 \text{ pF maximum}$	60		ns			
	$C_B = 400 \text{ pF maximum}$	120		ns			
t <sub>2</sub>	Standard mode	4.7		μs	t <sub>LOW</sub> , SCL low time		
	Fast mode	1.3		μs			
	High speed mode <sup>2</sup>						
	$C_B = 100 \text{ pF maximum}$	160		ns			
	$C_B = 400 \text{ pF maximum}$	320		ns			
t <sub>3</sub>	Standard mode	250		ns	t <sub>SU;DAT</sub> , data setup time		
	Fast mode	100		ns	·		
	High speed mode <sup>2</sup>	10		ns			
t <sub>4</sub> <sup>3</sup>	Standard mode	0	3.45	μs	t <sub>HD;DAT</sub> , data hold time		
	Fast mode	0	0.9	μs			
	High speed mode <sup>2</sup>			'			
	$C_B = 100 \text{ pF maximum}$	0	70	ns			
	$C_B = 400 \text{ pF maximum}$	0	150	ns			
<b>t</b> <sub>5</sub>	Standard mode	4.7		μs	t <sub>SU;STA</sub> , setup time for a repeated start condition		
	Fast mode	0.6		μs			
	High speed mode <sup>2</sup>	160		ns			
t <sub>6</sub>	Standard mode	4		μs	t <sub>HD;STA</sub> , hold time for a (repeated) start condition		
	Fast mode	0.6		μs	·		
	High speed mode <sup>2</sup>	160		ns			
t <sub>7</sub>	Standard mode	4.7		μs	t <sub>BUF</sub> , bus free time between a stop and a start condition		
	Fast mode	1.3		μs			
t <sub>8</sub>	Standard mode	4		μs	t <sub>su,sto</sub> , setup time for a stop condition		
	Fast mode	0.6		μs	·		
	High speed mode <sup>2</sup>	160		ns			
t <sub>9</sub>	Standard mode		1000	ns	t <sub>RDA</sub> , rise time of SDA signal		
	Fast mode	20 + 0.1 C <sub>B</sub>	300	ns			
	High speed mode <sup>2</sup>						
	$C_B = 100 \text{ pF maximum}$	10	80	ns			
	$C_B = 400 \text{ pF maximum}$	20	160	ns			
t <sub>10</sub>	Standard mode	<u> </u>	300	ns	t <sub>FDA</sub> , fall time of SDA signal		
	Fast mode	20 + 0.1 C <sub>B</sub>	300	ns			
	High speed mode <sup>2</sup>						
	$C_B = 100 \text{ pF maximum}$	10	80	ns			
	$C_B = 400 \text{ pF maximum}$	20	160	ns			

		ADG2188 I	Limit at T <sub>M</sub>	IN, T <sub>MAX</sub>	Description		
Parameter <sup>1</sup>	Conditions	Min	Max	Unit			
t <sub>11</sub>	Standard mode		1000	ns	t <sub>RCL</sub> , rise time of SCL signal		
	Fast mode	20 + 0.1 C <sub>B</sub>	300	ns			
	High speed mode <sup>2</sup>						
	$C_B = 100 pF maximum$	10	40	ns			
	C <sub>B</sub> = 400 pF maximum	20	80	ns			
t <sub>11A</sub>	Standard mode		1000	ns	t <sub>RCL1</sub> , rise time of SCL signal after a repeated start condition		
	Fast mode	20 + 0.1 C <sub>B</sub>	300	ns	and after an acknowledge bit		
	High speed mode <sup>2</sup>						
	C <sub>B</sub> = 100 pF maximum	10	80	ns			
	$C_B = 400 pF maximum$	20	160	ns			
t <sub>12</sub>	Standard mode		300	ns	t <sub>FCL</sub> , fall time of SCL signal		
	Fast mode	20 + 0.1 C <sub>B</sub>	300	ns			
	High speed mode <sup>2</sup>						
	C <sub>B</sub> = 100 pF maximum	10	40	ns			
	C <sub>B</sub> = 400 pF maximum	20	80	ns			
t <sub>SP</sub>	Fast mode	0	50	ns	Pulse width of suppressed spike		
	High speed mode <sup>2</sup>	0	10	ns			

<sup>1</sup> Guaranteed by initial characterization. All values measured with input filtering enabled. C8 refers to capacitive load on the bus line; tR and tF are measured between  $0.3~V_{DD}$  and  $0.7~V_{DD}$ .

### **TIMING DIAGRAM**

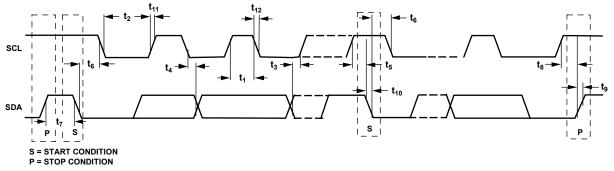


Figure 2. Timing Diagram for 2-Wire Serial Interface

<sup>&</sup>lt;sup>2</sup> High speed I<sup>2</sup>C is available only in -HS models <sup>3</sup> A device must provide a data hold time for SDA to bridge the undefined region of the SCL falling edge.

### **ABSOLUTE MAXIMUM RATINGS**

 $T_A = 25$ °C, unless otherwise noted.

Table 4

Table 4.	
Parameter	Rating
V <sub>DD</sub> to V <sub>SS</sub>	15 V
V <sub>DD</sub> to GND	−0.3 V to +15 V
V <sub>SS</sub> to GND	+0.3 V to −7 V
V <sub>L</sub> to GND	−0.3 V to +7 V
Analog Inputs	$V_{SS} - 0.3 \text{ V to } V_{DD} + 0.3 \text{ V}$
Digital Inputs	$-0.3 \text{ V to V}_{\text{L}} + 0.3 \text{ V or } 30 \text{ mA},$ whichever occurs first
Continuous Current	
10 V on Input; Single Input Connected to Single Output	65 mA
1 V on Input; Single Input Connected to Single Output	90 mA
10 V on Input; Eight Inputs Connected to Eight Outputs	25 mA
Operating Temperature Range	
Industrial (B Version)	–40°C to +85°C
Automotive (Y Version)	−40°C to +125°C
Storage Temperature Range	−65°C to +150°C
Junction Temperature	150°C
32-Lead LFCSP_VQ	
$\theta_{JA}$ Thermal Impedance	108.2°C/W
Reflow Soldering (Pb Free)	
Peak Temperature	260°C (+0/-5)
Time at Peak Temperature	10 sec to 40 sec

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### **ESD CAUTION**

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



## PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

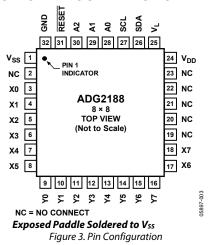


Table 5. Pin Function Descriptions<sup>1</sup>

Pin No.	Mnemonic	Description
1	Vss	Negative Power Supply in a Dual-Supply Application. For single-supply applications, this pin should be tied to GND.
2, 19 to 23	NC	No Connect.
3 to 8, 17, 18	X0 to X7	Can be inputs or outputs.
9 to 16	Y0 to Y7	Can be inputs or outputs.
24	$V_{DD}$	Positive Power Supply Input.
25	$V_L$	Logic Power Supply Input.
26	SDA	Digital I/O. Bidirectional open drain data line. External pull-up resistor required.
27	SCL	Digital Input, Serial Clock Line. Open drain input that is used in conjunction with SDA to clock data into the device. External pull-up resistor required.
28	A0	Logic Input. Address pin that sets the least significant bit of the 7-bit slave address.
29	A1	Logic Input. Address pin that sets the second least significant bit of the 7-bit slave address.
30	A2	Logic Input. Address pin that sets the third least significant bit of the 7-bit slave address.
31	RESET	Active Low Logic Input. When this pin is low, all switches are open, and appropriate registers are cleared to 0.
32	GND	Ground. Reference point for all circuitry on the ADG2188.

 $<sup>^{\, 1}</sup>$  It is recommended that the exposed paddle be soldered to  $V_{SS}$  to improve heat dissipation and crosstalk.

## TYPICAL PERFORMANCE CHARACTERISTICS

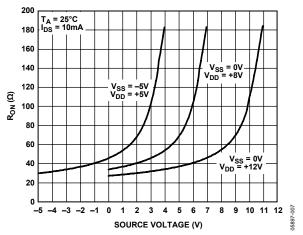


Figure 4. Signal Range

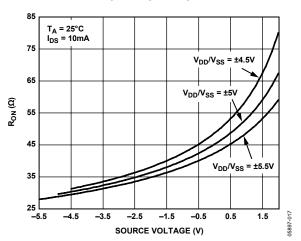


Figure 5. R<sub>ON</sub> vs. Source Voltage, Dual ±5 V Supplies

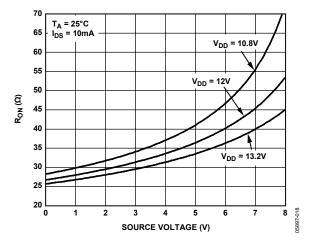


Figure 6.  $R_{ON}$  vs. Supplies,  $V_{DD} = 12 V \pm 10\%$ 

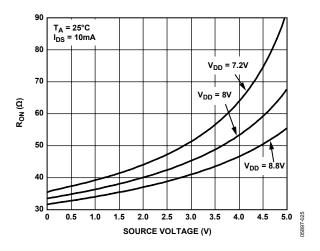


Figure 7.  $R_{ON}$  vs. Source Voltage,  $V_{DD}$  = 8 V  $\pm$  10%

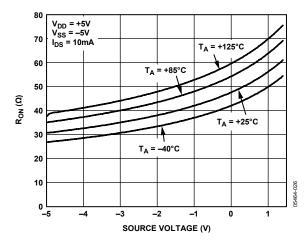


Figure 8.  $R_{ON}$  vs. Temperature, Dual  $\pm 5$  V Supplies

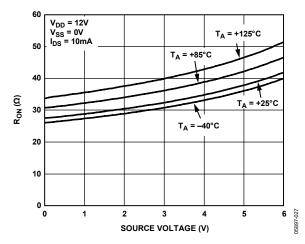


Figure 9.  $R_{ON}$  vs. Temperature,  $V_{DD} = 12 V$ 

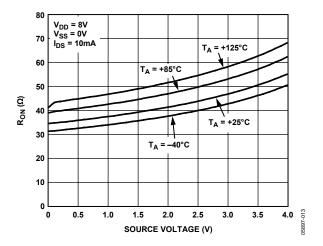


Figure 10.  $R_{ON}$  vs. Temperature,  $V_{DD} = 8 V$ 

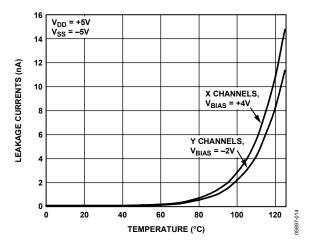


Figure 11. On Leakage vs. Temperature, Dual ±5 V Supplies

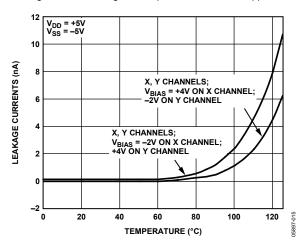


Figure 12. Off Leakage vs. Temperature, Dual ±5 V Supplies

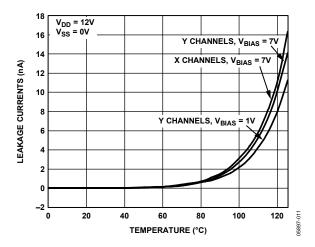


Figure 13. On Leakage vs. Temperature, 12 V Single Supply

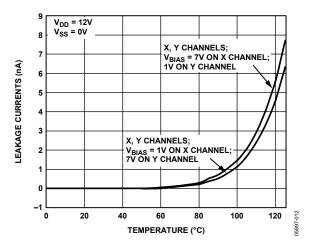


Figure 14. Off Leakage vs. Temperature, 12 V Single Supply

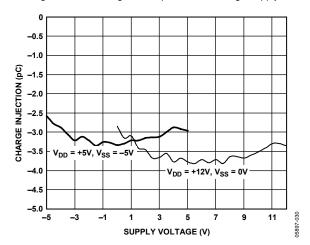


Figure 15. Charge Injection vs. Supply Voltage

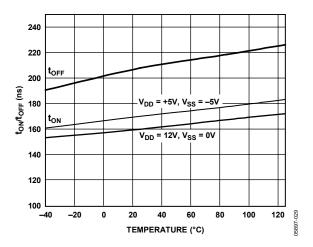


Figure 16. ton/toff Times vs. Temperature

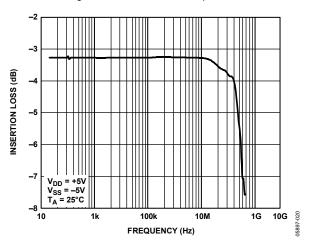


Figure 17. Individual Inputs to Individual Outputs Bandwidth, Dual ±5 V Supply

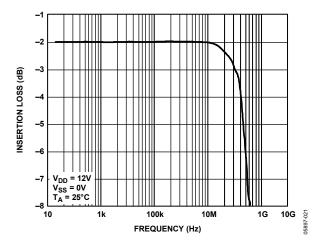


Figure 18. Individual Inputs to Individual Outputs Bandwidth, 12 V Single Supply

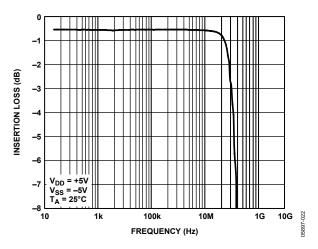


Figure 19. One Input to Eight Outputs Bandwidth, ±5 V Dual Supply

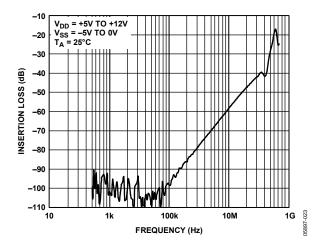


Figure 20. Off Isolation vs. Frequency

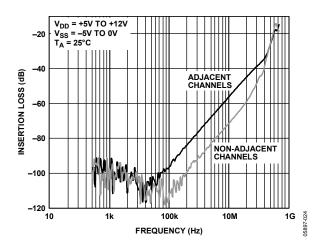


Figure 21. Crosstalk vs. Frequency

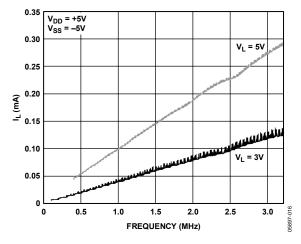


Figure 22. Digital Current (IL) vs. Frequency

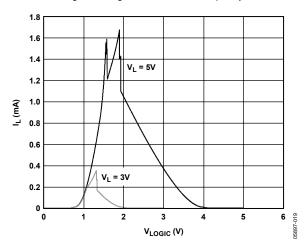


Figure 23. Digital Current ( $I_L$ ) vs.  $V_{LOGIC}$  for Varying Digital Supply Voltage

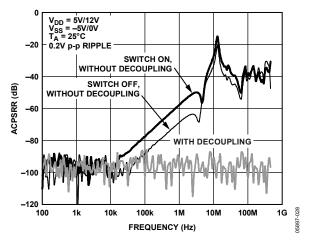
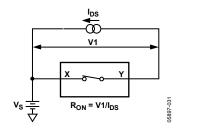
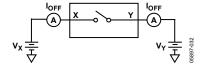


Figure 24. ACPSRR

## **TEST CIRCUITS**

The test circuits show measurements on one channel for clarity, but the circuit applies to any of the switches in the matrix.





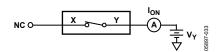


Figure 25. On Resistance

Figure 26. Off Leakage

Figure 27. On Leakage

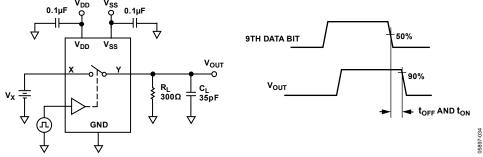
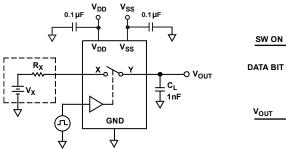


Figure 28. Switching Times, ton, toff



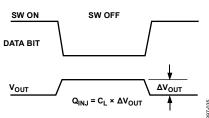


Figure 29. Charge Injection

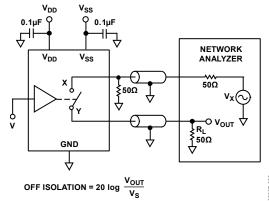
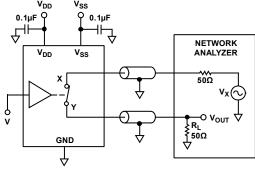


Figure 30. Off Isolation



INSERTION LOSS = 20  $\log \frac{V_{OUT} \text{ WITH SWITCH}}{V_{OUT} \text{ WITHOUT SWITCH}}$ 

Figure 31. Bandwidth

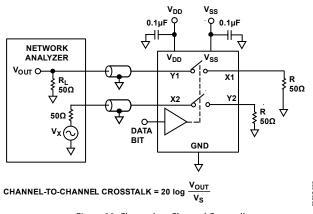


Figure 32. Channel-to-Channel Crosstalk

### **TERMINOLOGY**

### On Resistance (Ron)

The series on-channel resistance measured between the X input/output and the Y input/output.

### On Resistance Match ( $\Delta R_{ON}$ )

The channel-to-channel matching of on resistance when channels are operated under identical conditions.

#### On Resistance Flatness (R<sub>FLAT(ON)</sub>)

The variation of on resistance over the specified range produced by the specified analog input voltage change with a constant load current.

### Channel Off Leakage (I<sub>OFF</sub>)

The sum of leakage currents into or out of an off channel input.

#### Channel On Leakage (IoN)

The current loss/gain through an on-channel resistance, creating a voltage offset across the device.

#### Input Leakage Current (IIN)

The current flowing into a digital input when a specified low level or high level voltage is applied to that input.

### Input Off Capacitance (COFF)

The capacitance between an analog input and ground when the switch channel is off.

#### Input/Output On Capacitance (CoN)

The capacitance between the inputs or outputs and ground when the switch channel is on.

#### Digital Input Capacitance (C<sub>IN</sub>)

The capacitance between a digital input and ground.

### Output On Switching Time (ton)

The time required for the switch channel to close. The time is measured from 50% of the logic input change to the time the output reaches 10% of the final value.

### Output Off Switching Time (toff)

The time required for the switch to open. This time is measured from 50% of the logic input change to the time the output reaches 90% of the switch off condition.

### Total Harmonic Distortion + Noise (THD + N)

The ratio of the harmonic amplitudes plus noise of a signal to the fundamental.

#### -3 dB Bandwidth

The frequency at which the output is attenuated by 3 dB.

#### Off Isolation

The measure of unwanted signal coupling through an off switch.

#### Crosstalk

The measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

#### Differential Gain

The measure of how much color saturation shift occurs when the luminance level changes. Both attenuation and amplification can occur; therefore, the largest amplitude change between any two levels is specified and is expressed as a percentage of the largest chrominance amplitude.

#### **Differential Phase**

The measure of how much hue shift occurs when the luminance level changes. It can be a negative or positive value and is expressed in degrees of subcarrier phase.

#### **Charge Injection**

The measure of the glitch impulse transferred from the digital input to the analog output during on/off switching.

#### Input High Voltage (V<sub>INH</sub>)

The minimum input voltage for Logic 1.

#### Input Low Voltage (V<sub>INL</sub>)

The maximum input voltage for Logic 0.

#### Output Low Voltage (Vol.)

The minimum input voltage for Logic 1.

#### Input Low Voltage (V<sub>INL</sub>)

The maximum output voltage for Logic 0.

 $I_{DD}$ 

Positive supply current.

 $I_{ss}$ 

Negative supply current.

### THEORY OF OPERATION

The ADG2188 is an analog cross point switch with an array size of  $8 \times 8$ . The eight rows are referred to as the X input/output lines, and the eight columns are referred to as the Y input/output lines. The device is fully flexible in that it connects any X line or number of X lines with any Y line when turned on. Similarly, it connects any X line with any number of Y lines when turned on.

Control of the ADG2188 is carried out via an  $I^2C$  interface. The device can be operated from single supplies of up to 13.2 V or from dual  $\pm 5$  V supplies. The ADG2188 has many attractive features, such as the ability to reset all the switches, the ability to update many switches at the same time, and the option of reading back the status of any switch. All of these features are described in more detail here in the Theory of Operation section.

#### **RESET/POWER-ON RESET**

The ADG2188 offers the ability to reset all of the 64 switches to the off state. This is done through the RESET pin. When the RESET pin is low, all switches are open (off), and appropriate registers are cleared. Note that the ADG2188 also has a power-on reset block. This ensures that all switches are in the off condition at power-up of the device. In addition, all internal registers are filled with 0s and remain so until a valid write to the ADG2188 takes place.

#### LOAD SWITCH (LDSW)

LDSW is an active high command that allows a number of switches to be simultaneously updated. This is useful in applications where it is important to have synchronous transmission of signals. There are two LDSW modes: the transparent mode and the latched mode.

#### **Transparent Mode**

In this mode, the switch position changes after the new word is written into the input shift register. LDSW is set to 1.

#### **Latched Mode**

In this mode, the switch positions are not updated at the same time that the input registers are written to. This is achieved by setting LDSW to 0 for each word (apart from the last word) written to the device. Then, setting LDSW to 1 for the last word allows all of the switches in that sequence to be simultaneously updated.

#### **READBACK**

Readback of the switch array conditions is also offered when in standard mode and fast mode. Readback enables the user to check the status of the switches of the ADG2188. This is very useful when debugging a system.

### SERIAL INTERFACE

The ADG2188 is controlled via an I<sup>2</sup>C-compatible serial bus. The parts are connected to this bus as a slave device (no clock is generated by the switch).

#### HIGH SPEED I<sup>2</sup>C INTERFACE

In addition to standard and full speed I<sup>2</sup>C, the ADG2188 also supports the high speed (3.4 MHz) I<sup>2</sup>C interface. Only the –HS models provide this added performance. See the Ordering Guide for details.

#### **SERIAL BUS ADDRESS**

The ADG2188 has a 7-bit slave address. The four MSBs are hard coded to 1110, and the three LSBs are determined by the state of Pin A0, Pin A1, and Pin A2. By offering the facility to hardware configure Pin A0, Pin A1, and Pin A2, up to eight of these devices can be connected to a single serial bus.

The 2-wire serial bus protocol operates as follows:

1. The master initiates data transfer by establishing a start condition, defined as when a high-to-low transition on the SDA line occurs while SCL is high. This indicates that an address/data stream follows. All slave peripherals connected to the serial bus respond to the start condition and shift in the next eight bits, consisting of a 7-bit address (MSB first) plus an R/W bit that determines the direction of the data transfer, that is, whether data is written to or read from the slave device.

- 2. The peripheral whose address corresponds to the transmitted address responds by pulling the SDA line low during the ninth clock pulse, known as the acknowledge bit. At this stage, all other devices on the bus remain idle while the selected device waits for data to be written to or read from its serial register. If the R/W bit is 1 (high), the master reads from the slave device. If the R/W bit is 0 (low), the master writes to the slave device.
- 3. Data is transmitted over the serial bus in sequences of nine clock pulses: eight data bits followed by an acknowledge bit from the receiver of the data. Transitions on the SDA line must occur during the low period of the clock signal, SCL, and remain stable during the high period of SCL, because a low-to-high transition when the clock is high can be interpreted as a stop signal.
- 4. When all data bits have been read or written, a stop condition is established by the master. A stop condition is defined as a low-to-high transition on the SDA line while SCL is high. In write mode, the master pulls the SDA line high during the 10th clock pulse to establish a stop condition. In read mode, the master issues a no acknowledge for the ninth clock pulse (that is, the SDA line remains high). The master then brings the SDA line low before the 10th clock pulse and then high during the 10th clock pulse to establish a stop condition.

Refer to Figure 33 and Figure 34 for a graphical explanation of the serial data transfer protocol.

### **WRITING TO THE ADG2188**

#### **INPUT SHIFT REGISTER**

The input shift register is 24 bits wide. A 3-byte write is necessary when writing to this register and is done under the control of the serial clock input, SCL. The contents of the three bytes of the input shift register are shown in Figure 33 and described in Table 6.



**Table 6. Input Shift Register Bit Function Descriptions** 

Bit	Mnemonic	Description
DB23 to DB17	1110xxx	The MSBs of the ADG2188 are set to 1110. The LSBs of the address byte are set by the state of the three address pins, Pin A0, Pin A1, and Pin A2.
DB16	R/W	Controls whether the ADG2188 slave device is read from or written to.
		If $R/\overline{W} = 1$ , the ADG2188 is being read from.
		If $R/\overline{W} = 0$ , the ADG2188 is being written to.
DB15	Data	Controls whether the switch is to be open (off) or closed (on).  If Data = 0, the switch is open/off.
		If Data = 1, the switch is closed/on.
DB14 to DB11	AX3 to AX0	Controls I/Os X0 to X7. See Table 7 for the decode truth table.
DB10 to DB8	AY2 to AY0	Controls I/Os Y0 to Y7. See Table 7 for the decode truth table.
DB7 to DB1	X	Don't care.
DB0	LDSW	This bit is useful when a number of switches need to be updated simultaneously.  If LDSW = 1, the switch position changes after the new word is read in.  If LDSW = 0, the input data is latched, but the switch position is not changed.

As shown in Table 6, Bit DB11 to Bit DB14 control the X input/output lines, while Bit DB8 to Bit DB10 control the Y input/output lines. Table 7 shows the truth table for these bits. Note that the full coding sequence is written out for Channel Y0, and Channel Y1 to Channel Y7 follow a similar pattern. Note also that the RESET pin must be high when writing to the device.

Table 7. Address Decode Truth Table

DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	
DATA	AX3	AX2	AX1	AX0	AY2	AY1	AY0	Switch Configuration
1	0	0	0	0	0	0	0	X0 to Y0 (on)
0	0	0	0	0	0	0	0	X0 to Y0 (off)
1	0	0	0	1	0	0	0	X1 to Y0 (on)
0	0	0	0	1	0	0	0	X1 to Y0 (off)
1	0	0	1	0	0	0	0	X2 to Y0 (on)
0	0	0	1	0	0	0	0	X2 to Y0 (off)
1	0	0	1	1	0	0	0	X3 to Y0 (on)
0	0	0	1	1	0	0	0	X3 to Y0 (off)
1	0	1	0	0	0	0	0	X4 to Y0 (on)
0	0	1	0	0	0	0	0	X4 to Y0 (off)
1	0	1	0	1	0	0	0	X5 to Y0 (on)
0	0	1	0	1	0	0	0	X5 to Y0 (off)
Χ	0	1	1	0	0	0	0	Reserved
Χ	0	1	1	1	0	0	0	Reserved
1	1	0	0	0	0	0	0	X6 to Y0 (on)
0	1	0	0	0	0	0	0	X6 to Y0 (off)
1	1	0	0	1	0	0	0	X7 to Y0 (on)
0	1	0	0	1	0	0	0	X7 to Y0 (off)
Χ	1	0	1	0	0	0	0	Reserved
Χ	1	0	1	1	0	0	0	Reserved

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DB15 DATA	DB14 AX3	DB13 AX2	DB12 AX1	DB11 AX0	DB10 AY2	DB9 AY1	DB8 AY0	Switch Configuration
		_		_				
Χ	1	1	0	0	0	0	0	Reserved
Χ	1	1	0	1	0	0	0	Reserved
Χ	1	1	1	0	0	0	0	Reserved
Χ	1	1	1	1	0	0	0	Reserved
1	0	0	0	0	0	0	1	X0 to Y1 (on)
0	0	0	0	0	0	0	1	X0 to Y1 (off)
1	1	0	0	1	0	0	1	X7 to Y1 (on)
1	0	0	0	0	0	1	0	X0 to Y2 (on)
0	0	0	0	0	0	1	0	X0 to Y2 (off)
1	1	0	0	1	0	1	0	X7 to Y2 (on)
1	0	0	0	0	0	1	1	X0 to Y3 (on)
0	0	0	0	0	0	1	1	X0 to Y3 (off)
1	1	0	0	1	0	1	1	X7 to Y3 (on)
1	0	0	0	0	1	0	0	X0 to Y4 (on)
0	0	0	0	0	1	0	0	X0 to Y4 (off)
1	1	0	0	1	1	0	0	X7 to Y4 (on)
1	0	0	0	0	1	0	1	X0 to Y5 (on)
0	0	0	0	0	1	0	1	X0 to Y5 (off)
1	1	0	0	1	1	0	1	X7 to Y5 (on)
1	0	0	0	0	1	1	0	X0 to Y6 (on)
0	0	0	0	0	1	1	0	X0 to Y6 (off)
1	1	0	0	1	1	1	0	X7 to Y6 (on)
1	0	0	0	0	1	1	1	X0 to Y7 (on)
0	0	0	0	0	1	1	1	X0 to Y7 (off)
1	1	0	0	1	1	1	1	X7 to Y7 (on)

#### **WRITE OPERATION**

When writing to the ADG2188, the user must begin with an address byte and  $R/\overline{W}$  bit, after which the switch acknowledges that it is prepared to receive data by pulling SDA low. This address byte is followed by the two 8-bit words. The write operations for the switch array are shown in Figure 34. Note that it is only the condition of the switch corresponding to the bits in the data bytes that changes state. All other switches retain their previous condition.

#### **READ OPERATION**

Readback on the ADG2188 is designed to work as a tool for debug and can be used to output the status of any of the 64 switches of the device. The readback function is a two-step sequence that works as follows:

- Select the relevant X line to be read back from. Note that
  there are eight switches connecting that X line to the eight
  Y lines. The next step involves writing to the ADG2188 to
  tell the part to reveal the status of those eight switches.
  - a. Enter the I<sup>2</sup>C address of the ADG2188, and set the  $R/\overline{W}$  to 0 to indicate a write to the device.

- b. Enter the readback address for the X line of interest, the addresses of which are shown in Table 8. Note that the ADG2188 is expecting a 2-byte write; therefore, be sure to also enter another byte of don't cares (see Figure 35).
- c. The ADG2188 then places the status of those eight switches in a register than can be read back.
- 2. The second step involves reading back from the register that holds the status of the eight switches associated with the X line of choice.
  - a. As before, enter the  $I^2C$  address of the ADG2188. This time, set the  $R/\overline{W}$  to 1 to indicate a read back from the device.
  - d. As with a write to the device, the ADG2188 outputs a 2-byte sequence during readback. Therefore, the first eight bits of data out that are read back are all 0s. The next eight bits of data that come back are the status of the eight Y lines attached to that particular X line. If the bit is a 1, then the switch is closed (on); similarly, if the bit is a 0, the switch is open (off).

The entire read sequence is shown in Figure 35.

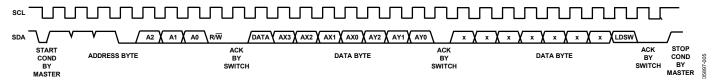


Figure 34. Write Operation

Table 8. Readback Addresses for Each X Line

X Line	RB7	RB6	RB5	RB4	RB3	RB2	RB1	RB0
X0	0	0	1	1	0	1	0	0
X1	0	0	1	1	1	1	0	0
X2	0	1	1	1	0	1	0	0
Х3	0	1	1	1	1	1	0	0
X4	0	0	1	1	0	1	0	1
X5	0	0	1	1	1	1	0	1
Х6	0	1	1	1	0	1	0	1
X7	0	1	1	1	1	1	0	1

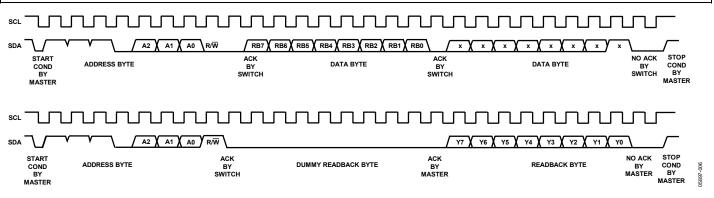


Figure 35. Read Operation

### **EVALUATION BOARD**

The ADG2188 evaluation board allows designers to evaluate the high performance  $8 \times 8$  switch array of the ADG2188 with a minimum of effort.

The evaluation kit includes a populated, tested ADG2188 printed circuit board. The evaluation board interfaces to the USB port of a PC, or it can be used as a standalone evaluation board. Software is available with the evaluation board that allows the user to easily program the ADG2188 through the USB port. Schematics of the evaluation board are shown in Figure 36 and Figure 37. The software runs on any PC that has Microsoft\* Windows\* 2000 or Windows XP installed.

#### **USING THE ADG2188 EVALUATION BOARD**

The ADG2188 evaluation kit is a test system designed to simplify the evaluation of the ADG2188. Each input/output of the part comes with a socket specifically chosen for easy audio/video evaluation. An application note is also available with the evaluation board that gives full information on operating the evaluation board.

#### **POWER SUPPLY**

The ADG2188 evaluation board can be operated with both single and dual supplies.  $V_{\rm DD}$  and  $V_{SS}$  are supplied externally by the user. The  $V_L$  supply can be applied externally, or the USB port can be used to power the digital circuitry.

### **SCHEMATICS**



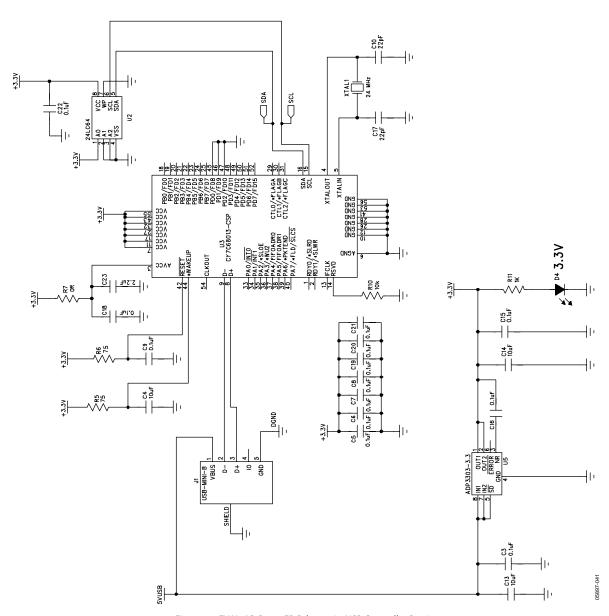


Figure 36. EVAL-ADG2188EB Schematic, USB Controller Section

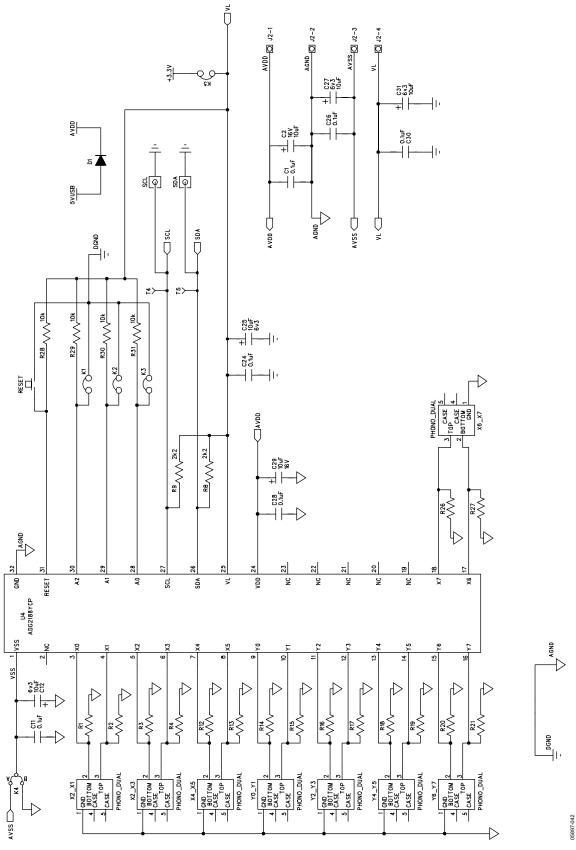
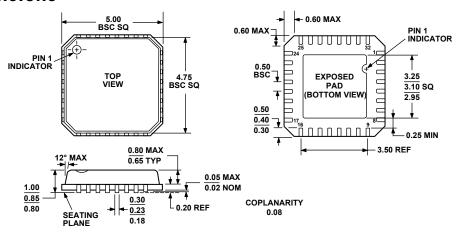


Figure 37. EVAL-ADG2188EB Schematic, Chip Section

## **OUTLINE DIMENSIONS**



#### COMPLIANT TO JEDEC STANDARDS MO-220-VHHD-2

Figure 38. 32-Lead Lead Frame Chip Scale Package [LFCSP\_VQ] 5 mm x 5 mm Body, Very Thin Quad (CP-32-2) Dimensions shown in millimeters

### **ORDERING GUIDE**

	Temperature			Package
Model	Range	I <sup>2</sup> C Speed	Package Description	Option
ADG2188BCPZ-R2 <sup>1</sup>	-40°C to +85°C	100 kHz, 400 kHz	32-Lead Lead Frame Chip Scale Package [LFCSP_VQ]	CP-32-2
ADG2188BCPZ-REEL7 <sup>1</sup>	-40°C to +85°C	100 kHz, 400 kHz	32-Lead Lead Frame Chip Scale Package [LFCSP_VQ]	CP-32-2
ADG2188BCPZ-HS-RL7 <sup>1</sup>	-40°C to +85°C	100 kHz, 400 kHz, 3.4 MHz	32-Lead Lead Frame Chip Scale Package [LFCSP_VQ]	CP-32-2
ADG2188YCPZ-R2 <sup>1</sup>	-40°C to +125°C	100 kHz, 400 kHz	32-Lead Lead Frame Chip Scale Package [LFCSP_VQ]	CP-32-2
ADG2188YCPZ-REEL7 <sup>1</sup>	-40°C to +125°C	100 kHz, 400 kHz	32-Lead Lead Frame Chip Scale Package [LFCSP_VQ]	CP-32-2
ADG2188YCPZ-HS-RL7 <sup>1</sup>	-40°C to +125°C	100 kHz, 400 kHz, 3.4 MHz	32-Lead Lead Frame Chip Scale Package [LFCSP_VQ]	CP-32-2
EVAL-ADG2188EB			8 x 8 Evaluation Board	

 $<sup>^{1}</sup>$  Z = Pb-free part.

## **NOTES**

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